

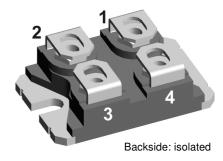
### **FRED**

1200 V 91 A 40 ns

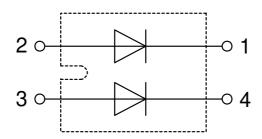
Fast Recovery Epitaxial Diode Low Loss and Soft Recovery Parallel legs

Part number

DSEI2x101-12A







### Features / Advantages:

- Planar passivated chips
- Low leakage current
- · Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0 • Base plate: Copper
- internally DCB isolated
- Advanced power cycling

#### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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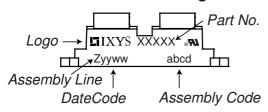


Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V <sub>RRM</sub>	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 1200 V	$T_{VJ} = 25^{\circ}C$			3	mA
		$V_R = 960 V$	$T_{VJ} = 125^{\circ}C$			15	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 100 A	$T_{VJ} = 25^{\circ}C$			1.87	V
		$I_F = 200 A$				2.13	٧
		I <sub>F</sub> = 100 A	T <sub>VJ</sub> = 150°C			1.61	V
		$I_F = 200 A$				1.92	٧
I FAV	average forward current	$T_{C} = 50^{\circ}C$	T <sub>VJ</sub> = 150°C			91	Α
		rectangular $d = 0.5$					
V <sub>F0</sub>	threshold voltage		$T_{VJ} = 150$ °C			1.01	V
$\mathbf{r}_{F}$	slope resistance	calculation only				6.1	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	9				0.5	K/W
R <sub>thCH</sub>	thermal resistance case to heatsin	ık			0.10		K/W
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			250	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			900	Α
CJ	junction capacitance	$V_R = 400  \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		107		pF
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		38		Α
		$I_F = 100 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 100^{\circ}C$		52		Α
t <sub>rr</sub>	reverse recovery time	$I_F = 100 \text{ A}; V_R = 600 \text{ V}$ $-\text{di}_F / \text{dt} = 600 \text{ A} / \mu \text{s}$	$T_{VJ} = 25 ^{\circ}\text{C}$		150		ns
	J	1	$T_{VJ} = 100^{\circ}C$		255		ns



Package SOT-227B (minibloc)				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					150	Α
T <sub>VJ</sub>	virtual junction temperature	9			-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		150	°C
Weight						30		g
M <sub>D</sub>	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{\scriptscriptstyleT}$	terminal torque				1.1		1.5	Nm
d <sub>Spp/App</sub>	creepage distance on surface   striking distance through ai	terminal to terminal	10.5	3.2			mm	
d <sub>Spb/Apb</sub>	creepage distance on suna	ace   striking distance through an	terminal to backside	8.6	6.8			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second	50/60 Hz, RMS; IsoL ≤ 1 mA		3000			٧
		t = 1 minute			2500			٧

## **Product Marking**

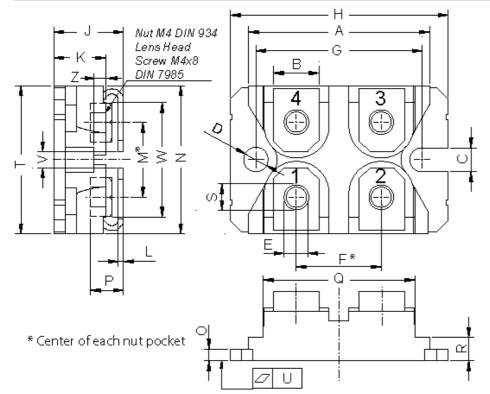


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x101-12A	DSEI2x101-12A	Tube	10	468002

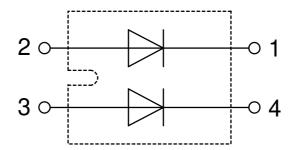
<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	$R_0$	Fast Diode		
V <sub>0 max</sub>	threshold voltage	1.01		V
$R_{\text{0 max}}$	slope resistance *	4.9		$m\Omega$



### Outlines SOT-227B (minibloc)



Dim.	Millir	neter	Inches	
Dim.	min	max	min	max
Α	31.50	31.88	1.240	1.255
В	7.80	8.20	0.307	0.323
С	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
Е	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
Н	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
0	1.95	2.13	0.077	0.084
Р	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
Т	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Ζ	2.50	2.70	0.098	0.106





### **Fast Diode**

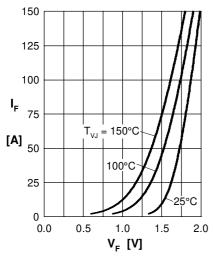


Fig. 1 Forward current I<sub>F</sub> versus V<sub>F</sub>

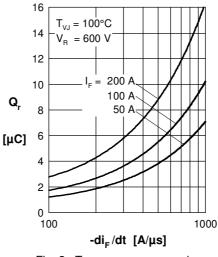


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$ 

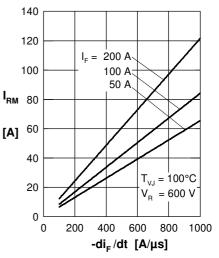


Fig. 3 Typ. peak reverse current  $I_{\rm rr}$  versus  $-{\rm di_F}/{\rm dt}$ 

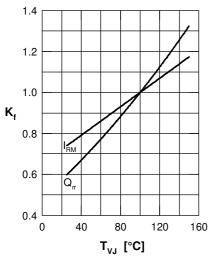


Fig. 4 Dyn. parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$ 

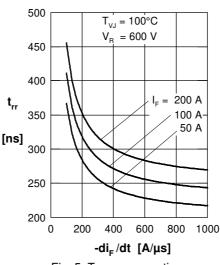


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_{F}/dt$ 

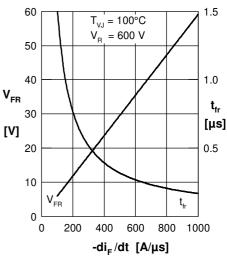


Fig. 6 Typ. peak forward voltage  $V_{FB}$  and  $t_{fr}$  versus  $di_{F}/dt$ 

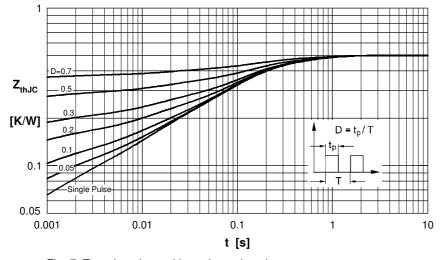


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$	t <sub>i</sub>
	[K/W]	[s]
1	0.020	0.00002
2	0.050	0.00081
3	0.076	0.01000
4	0.240	0.09400
5	0.114	0.45000

# **Mouser Electronics**

**Authorized Distributor** 

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IXYS:

DSEI2x101-12A